

CLAIMS

What is claimed is

1. A method for reducing line edge roughness of photoresist,
5 comprising:

providing a photoresist, said photoresist at least having a
trench; and

filling said trenches, said trenches being totally filled by an
additional material.

10 2. The method of claim 1, said trenches are located on
sidewall of said photoresist.

15 3. The method of claim 1, said trenches are located on this
top of said photoresist.

4. The method of claim 1, said additional material being
adhered to said photoresist.

20 5. The method of claim 1, said additional material being
adhered to said photoresist by a chemical reaction.

25 6. The method of claim 1, said additional material being
adhered to said photoresist by a physical reaction.

7. The method of claim 1, wherein available method for
filling said trenches with said additional material is chosen from the
group consisting of spin coating, dip, and spray.

8. The method of claim 1, said additional material being a fluid material.

9. The method of claim 1, said additional material being
5 chosen from the group consisting of solution and suspension.

10. The method of claim 1, said additional material being thermosetting polymer.

10 11. The method of claim 1, said additional material being thermoplasticity polymer.

12. The method of claim 1, said additional material could be reacted with a hydroxyl group or proton of said photoresist.

15 13. The method of claim 1, said additional material being chosen from the group consisting of PMMA, POLY IMIDE, RELACS, material with a plurality of -NH groups, and material with a plurality of -OH groups.

20 14. A method for reducing line edge roughness of photoresist, comprising:

providing a photoresist which at least having a trench;

25 filling said trenches so let that said trenches are totally filled by an additional material; and

treating said additional material so let that adhesion between said additional material and said photoresist is enhanced after said additional material is treated.

15. The method of claim 14, said trenches being located on
sidewall of said photoresist.

16. The method of claim 14, said trenches being located on
5 top of said photoresist.

17. The method of claim 6, wherein available method for
treating said additional material is chosen from the group consisting of
thermal treatment, ultraviolet light curing, electrons beam curing,
10 treatment of chemical reaction, and chemical reaction between a
plurality of functional groups of said photoresist and a plurality of
functional groups of said additional materials.

18. A method for reducing line edge roughness of photoresist,
15 comprising:

providing a photoresist, said photoresist at least having a
trench and being located on a substrate;

filling said trenches, said trenches being totally filled by an
additional material; and

20 removing part of said additional material, removed part of said
additional material being located on said photoresist and said substrate.

19. The method of claim 18, wherein available method for
filling said trenches with said additional material is chosen from the
25 group consisting of spin coating, dip, and spray.

20. The method of claim 18, wherein available method for
removing part of said additional material is chosen from the group
consisting of thermal treatment and spin.